

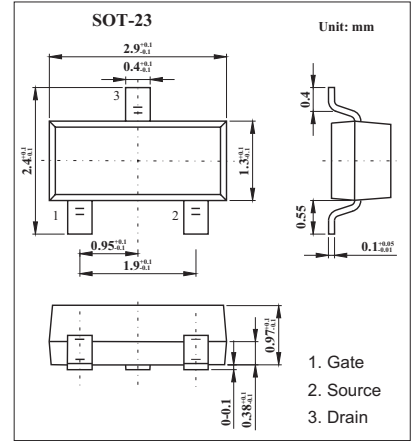
SOT-23 Plastic-Encapsulate MOSFETS

Features

- 1.8-V Rated
- RoHS Compliant
- N-Channel 20 -V (D-S) MOSFET

MECHANICAL DATA

- Case style:SOT-23molded plastic
- Mounting position:any



MAXIMUM RATINGS AND CHARACTERISTICS

@ 25°C Ambient Temperature (unless otherwise noted)

Parameter	Symbol	5 sec	Steady State	Unit
Drain-Source Voltage	V _{DS}		20	V
Gate-Source Voltage	V _{GS}		±8	V
Continuous Drain Current (T _J =150°C) *2 T _A =25°C T _A =70°C	I _D	4.9 3.9	3.77 3.0	A
Pulsed Drain Current *2	I _{DM}		15	A
Avalanche Current*2 L = 0.1 mH	I _{AS}		15	A
Single Avalanche Energy L = 0.1 mH	E _{AS}		11.25	mJ
Continuous Source Current (diode conduction) *2	I _S		1.0	A
Power Dissipation *2 T _A =25°C T _A =70°C	P _D	1.25 0.8	0.75 0.48	W
Jumction Temperature and Storage Temperature	T _j ,T _{stg}		-55 to 150	°C

*1 Surface Mounted on 1□x 1□FR4 Board.

*2 Pulse width limited by maximum junction temperature

Thermal Resistance Ratings

Parameter	Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient * t ≤ 5 sec	R _{thJA}	75	100	°C/W
Maximum Junction-to-Ambient * Steady State		120	166	
Maximum Junction-to-Foot Steady State	R _{thJF}	40	50	

* Surface Mounted on 1□x 1□FR4 Board.

MOSFET ELECTRICAL CHARACTERISTICS $T_a=25\text{ }^\circ\text{C}$ unless otherwise specified

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	20			V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	0.45	0.65	0.85	
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 8\text{ V}$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 20\text{ V}, V_{GS} = 0\text{ V}$			1	$\mu\text{ A}$
		$V_{DS} = 20\text{ V}, V_{GS} = 0\text{ V}, T_J = 70\text{ }^\circ\text{C}$			75	
On-State Drain Current	$I_{D(on)}$	$V_{DS} \geq 10\text{ V}, V_{GS} = 4.5\text{ V}$	15			A
Drain-Source On-State Resistance *	$r_{DS(on)}$	$V_{GS} = 4.5\text{ V}, I_D = 5.0\text{ A}$		0.027	0.033	Ω
		$V_{GS} = 2.5\text{ V}, I_D = 4.5\text{ A}$		0.033	0.040	
		$V_{DS} = 1.8\text{ V}, I_D = 4.0\text{ A}$		0.042	0.051	
Forward Transconductance *	g_{fs}	$V_{DS} = 15\text{ V}, I_D = 5.0\text{ A}$		40		S
Diode Forward Voltage *	V_{SD}	$I_S = 1.0\text{ A}, V_{GS} = 0\text{ V}$		0.8	1.2	V
Total Gate Charge	Q_g	$V_{DS} = 10\text{ V}, V_{GS} = 4.5\text{ V}, I_D = 5.0\text{ A}$		11.2	14	nC
Gate-Source Charge	Q_{gs}			1.4		
Gate-Drain Charge	Q_{gd}			2.2		
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 10\text{ V}, R_L = 10\Omega, I_D = 1\text{ A}, V_{GEN} = -4.5\text{ V}, R_G = 6\Omega$		15	25	ns
Rise Time	t_r			40	60	
Turn-Off Delay Time	$t_{d(off)}$			48	70	
Fall-Time	t_f			31	45	
Source-Drain Reverse Recovery Time	t_{rr}	$I_F = 1.0\text{ A}, di/dt = 100\text{ A}/\mu\text{s}$		13	25	

*Pulse test: $PW \leq 300\mu\text{s}$ duty cycle $\leq 2\%$.

Marking	C2
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